

Preliminary Specifications Subject to Change without Notice

DESCRIPTION

JW7726HAD is a synchronous rectifier, used for the secondary side rectification of isolation topologies, such as Active Clamp Flyback and CCM/QR/DCM Flyback. JW7726HAD is able to significantly improve the efficiency comparing with the conventional Diode rectifier.

When JW7726HAD senses V_{ds} of MOSFET less than -140mV, it turns on the internal MOSFET. Once the V_{ds} is greater than -6mV, JW7726HAD turns off the internal MOSFET.

JW7726HAD supports multiple operation modes, such as DCM, CrCM, CCM and Quasi-Resonant. By implementing the Joulwatt proprietary technology, JW7726HAD is able to handle CCM operation.

JW7726HAD is available in PVDFN5*6-8 package.

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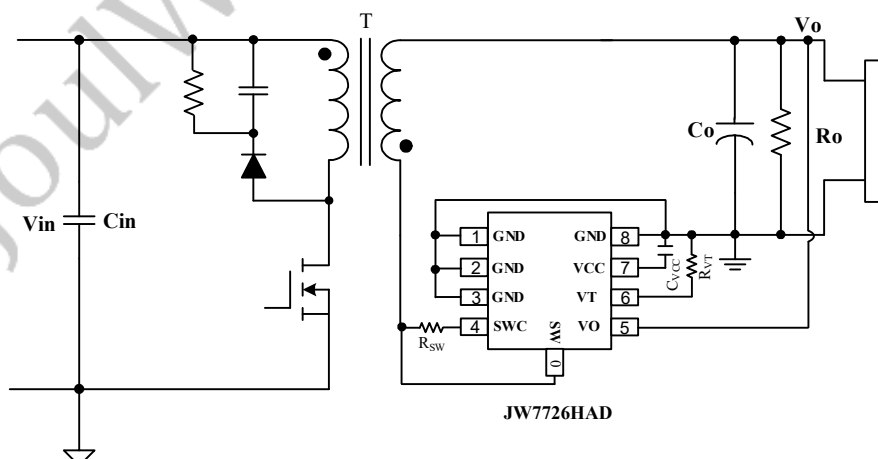
FEATURES

- Supports Active Clamp Flyback, DCM, Quasi-Resonant, and CCM Flyback
- Support High-side and Low-side Rectification
- Output Voltage Directly Supply VCC
- Low Quiescent Current
- Fast Driver Capability for CCM Operation
- PVDFN5*6-8 Package

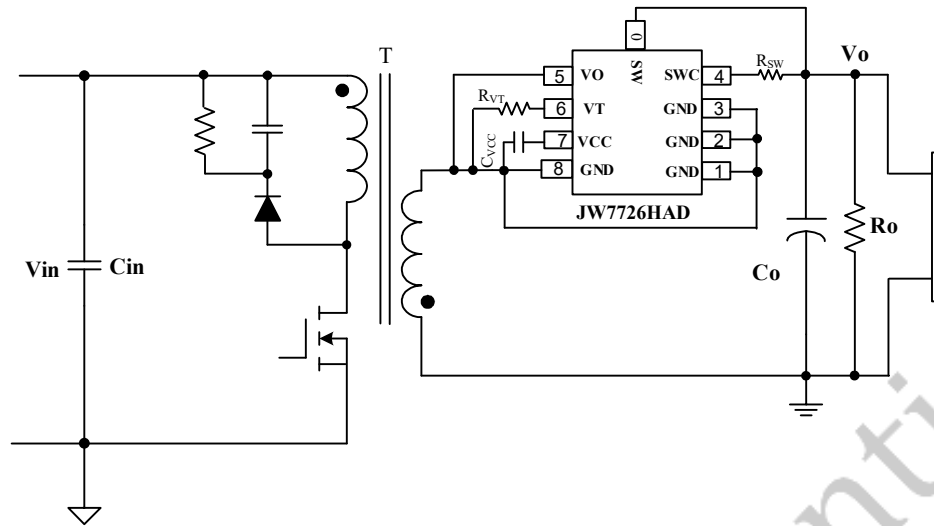
APPLICATIONS

- Active Clamp Flyback and Flyback Converters
- Adaptor
- LCD and PDP TV

TYPICAL APPLICATION



JW7726HAD Typical Application for Low-side

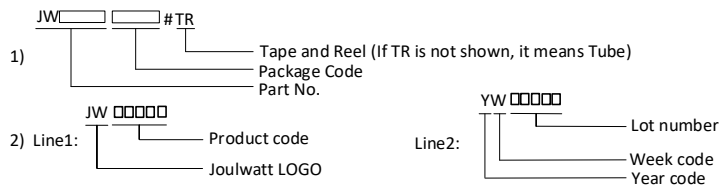


JW7726HAD Typical Application for High-side.

ORDER INFORMATION

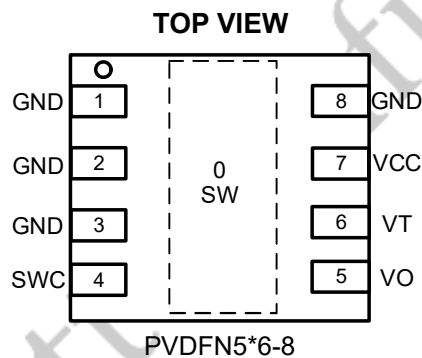
DEVICE ¹⁾	PACKAGE	TOP MARKING ²⁾	ENVIRONMENTAL ³⁾
JW7726HADPVDLQF#TR	PVDFN5*6-8	JW7726HAD YW□□□□□	Green

Notes:



3) All Joulwatt products are packaged with Pb-free and Halogen-free materials and compliant to RoHS standards.

PIN CONFIGURATION

ABSOLUTE MAXIMUM RATING¹⁾

SW PIN	100V
SWC PIN	-1 to 100V
VO PIN	-0.3 to 28V
VCC PIN.....	-0.3 to 9V
VT PIN.....	-0.3 to 7V
Junction Temperature ^{2) 3)}	150°C
Lead Temperature	260°C
Storage Temperature.....	-65°C to 150°C
Continuous Power Dissipation($T_A=+25^{\circ}\text{C}$) ⁴⁾ ESOP-8.....	2.5W
ESD Susceptibility (Human Body Model)	2kV

RECOMMENDED OPERATING CONDITIONS

SW Pin.....	4.7V to 80V
SWC Pin.....	4.7V to 80V
VO Pin.....	4.7V to 25V
VCC PIN.....	4V to 8.5V
Operation Junction Temperature(T _J).....	-40°C to 125°C

THERMAL PERFORMANCE⁵⁾

	θ_{JA}	θ_{JC}
PVDFN5*6-8.....	50.....	3°C/W

Note:

- 1) Exceeding these ratings may damage the device. These stress rating do not imply function operation of the device at any other conditions beyond those indicated under RECOMMENDED OPERATING CONDITIONS.
- 2) Continuous operation over the specified absolute maximum operating junction temperature may damage the device.
- 3) The device is not guaranteed to function outside of its operating conditions.
- 4) The maximum allowable continuous power dissipation at any ambient temperature is calculated by $P_D(MAX)=(T_J(MAX)-T_A)/ \theta_{JA}$.
- 5) Measured on JESD51-7, 4-layer PCB.

ELECTRICAL CHARACTERISTICS

TA = 25°C, unless otherwise stated

Advance Information, not production data, subject to change without notice.

Item	Symbol	Condition	Min.	Typ.	Max.	Units
VCC Section						
VCC Voltage	VCC	SW=40V, VCC=2.2uF	7.4	7.9	8.4	V
VCC Startup Voltage	V _{CC_Startup}		4.2	4.5	4.8	V
VCC UVLO	V _{CC_UVLO}		3.7	3.95	4.2	V
Operation Current (GT On)	I _{VCC}	GT=5nF, VCC=2.2uF	0.65	1.05	1.35	mA
Quiescent Current	I _q	VCC=4.5V, VCC=2.2uF		110		uA
SWC and VO Section						
Internal MOS Turn on Threshold	V _{MOS_ON}		-170	-140	-110	mV
Internal MOS Turn off Threshold ⁶⁾	V _{MOS_OFF}			-6		mV
Internal MOS Minimum on Time ⁶⁾	T _{MIN_ON}			560		ns
Turn-on Total Delay ⁶⁾	T _{DON}			50		nS
Turn-off Total Delay ⁶⁾	T _{DOF}			20		nS
VCC Charge Current	I _{SW_CHG}	SW=40V, VCC=6V	75	95		mA
VO Enable Charge Voltage	V _{O_EN}	VCC=4V, SW=0V, rising	4.48	4.6	4.8	V
VO Disable Charge Voltage	V _{O_DIS}	VCC=4V, SW=0V, falling	4.4	4.55	4.7	V
VO Charge Current	I _{VO_CHG}	SW=0V, VCC=6V, VO=12V	28	40	52	mA
Internal MOSFET(SW) Section						
Internal MOSFET Rdson	Rdson	VGT=10V		10		mΩ
Breakdown Voltage	B _{(BR)DSS}		100			V

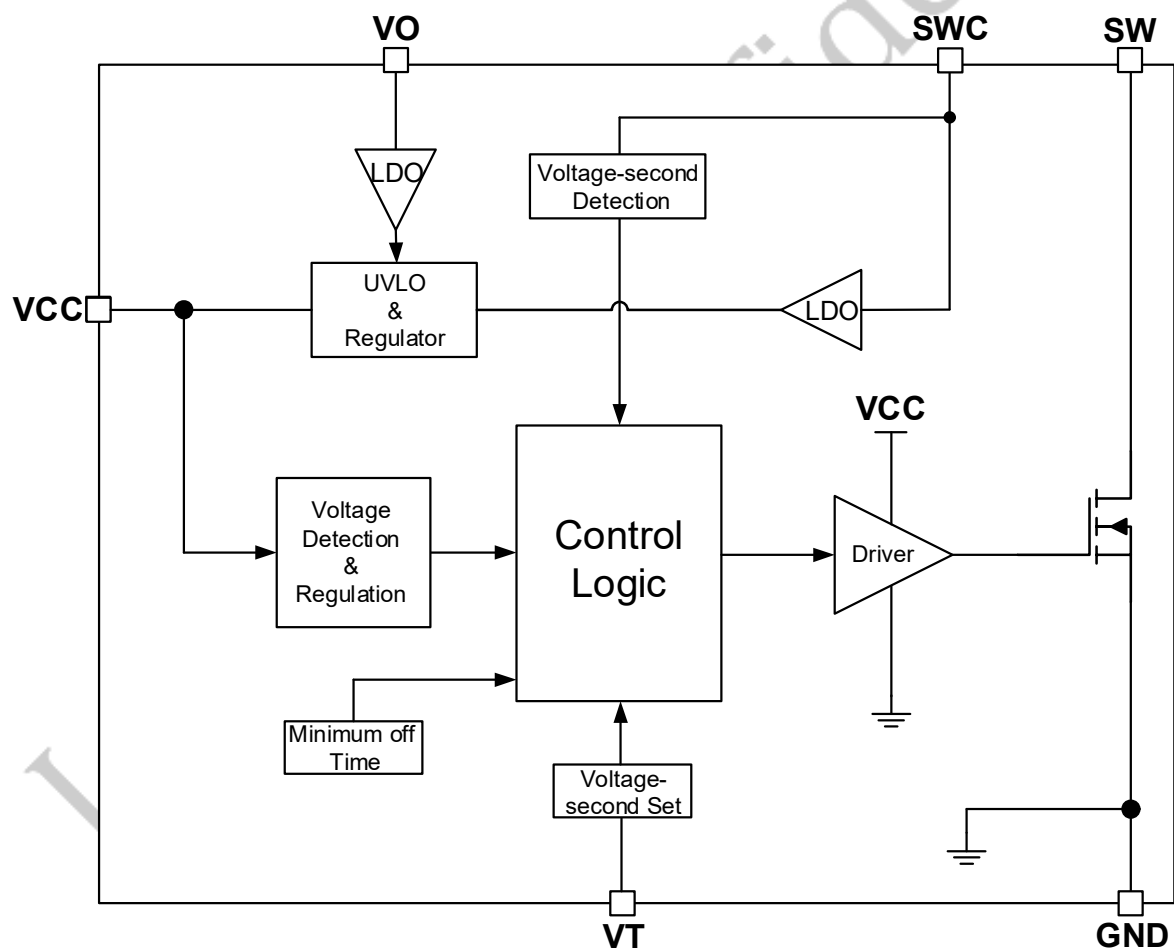
Note:

6) Guaranteed by design.

PIN DESCRIPTION

Pin	Name	Description
1,2,3,8	GND	Ground.
4	SWC	Internal Power MOSFET Drain Voltage Sensing. Charging to VCC.
5	VO	Output Voltage Sensing and Charging to VCC.
6	VT	Set the Voltage-second Product.
7	VCC	Power Supply. Bypass a Capacitor Between VCC and GND.
0	SW	Internal Power MOSFET Drain.

BLOCK DIAGRAM



FUNCTIONAL DESCRIPTION

Operation

JW7726HAD is a synchronous rectifier combined with internal MOSFET can replace the Schottky Barrier Diode. It supports all operations, such as DCM, CrCM, (Quasi-Resonant) and CCM when adopted in Active Clamp Flyback and Flyback converters.

Startup

During the startup period, when the VCC is charged up by the two internal LDOs connected to SW and VO pin respectively.

When VO is lower than V_{O_EN} (falling), JW7726HAD can power itself through the internal LDO connected to SW pin during the SR turn-off period, which means primary the primary side MOSFET is turned on and SW presents a positive voltage. A capacitor between VCC and GND is required to store the energy and supply to IC during the SR turn-on period.

When VO is above V_{O_EN} (rising), the VO pin charges VCC pin.

Once the VCC voltage exceeds $V_{CC_Startup}$, the JW7726HAD exits the UVLO. If VCC is lower than V_{CC_UVLO} , the internal MOSFET is turned off. The current flows through body diode before the VCC reaches to the startup voltage $V_{CC_startup}$.

Under-Voltage Lockout (UVLO)

When the VCC is below UVLO threshold, the internal MOSFET is turned off and pulled low internally. Once the VCC exceeds the startup voltage $V_{CC_startup}$, the parts is activated again.

Turn On Phase

There are two conditions for the JW7726HAD to turn on the internal MOSFET, i.e. V_{SW} , voltage-second value on SW pin when primary side switch is on, and the turn on phase is shown in Fig. 1.

1) V_{SW} : when the synchronous MOSFET is conducting, current flows through the body diode of MOSFET, which generates a negative voltage V_{SW} across it. When V_{SW} is lower than V_{MOS_ON} , the part will pull the gate high to turn on the synchronous MOSFET after turn on delay time T_{DON} if the other condition is met.

2) Volt-second of SW: in DCM and QR operation, there are parasitic oscillations. In some applications, the drain resonant voltage may fall below the SR turn on threshold, especially for the first couple rings. SR could be falsely turned on, which may cause shoot through issue and result in high power loss. The volt-second value of SW pin can be used to distinguish the parasitic ring from normal primary side switch on. The threshold can be set by the resistance at VT pin. The curve is shown in Fig. 2.

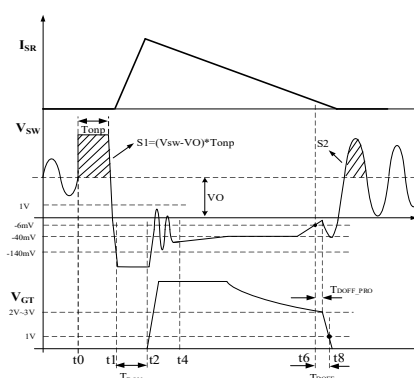


Fig. 1 Turn on delay and turn off delay

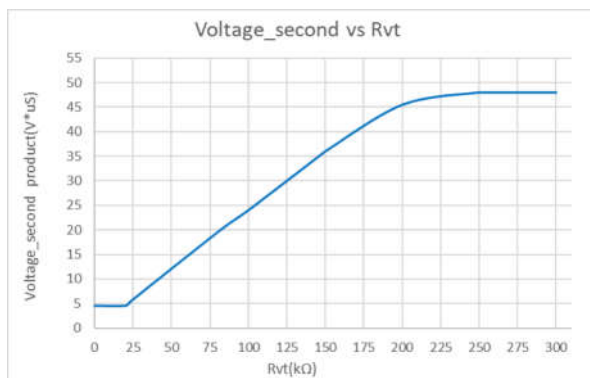


Fig. 2 Volt-second value vs. VT resistance

Minimum On Time (MOT)

When the synchronous MOSFET is turn on, there is a minimum on time for the SR. The V_{SW} voltage may have a parasitic ring when the synchronous MOSFET turns on. So, a minimum on time (MOT) is very important to avoid the MOSFET turn off threshold is false triggered.

Conducting Phase

When the synchronous MOSFET is turned on, the drain source voltage V_{SW} it is determined by its on resistance and the current through it. The part adjusts the gate voltage and regulates the V_{SW} to the internal threshold (typical -40mV) after the synchronous MOSFET turn on. When the V_{SW} is lower than -40mV, the gate keeps its maximum voltage. And the synchronous MOSFET is fully on.

The V_{SW} rises when the current follow through the MOSFET decreases. The gate voltage will be decreased to increase its on resistance and regulate the V_{SW} around -40mV.

It should be noted that the typical regulation threshold (-40mV) during MOSFET on time is not fixed, it can be internally changed to ensure the proper operation under CCM mode.

Turn Off Phase

After synchronous MOSFET conducting, once the voltage V_{SW} touches the MOSFET turn off threshold, the gate is pulled to low after a turn off delay time T_{DOFF} .

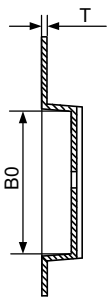
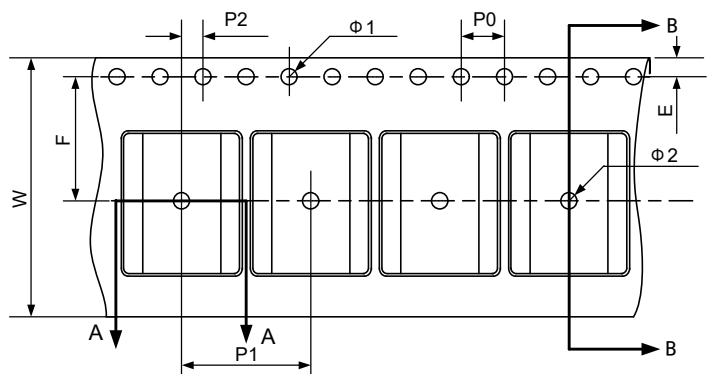
Output Voltage Detection

The JW7726HAD has output voltage detection function via VO pin. VCC is charged from VO pin when VO is higher than V_{O_EN} to save power loss caused by the LDO when charging from SW pin to VCC pin. When VO drops below V_{O_DIS} , the JW7726HAD is powered from SW pin.

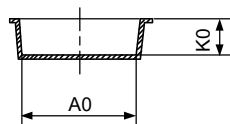
TAPE AND REEL INFORMATION

Carrier Tape

UNIT: mm



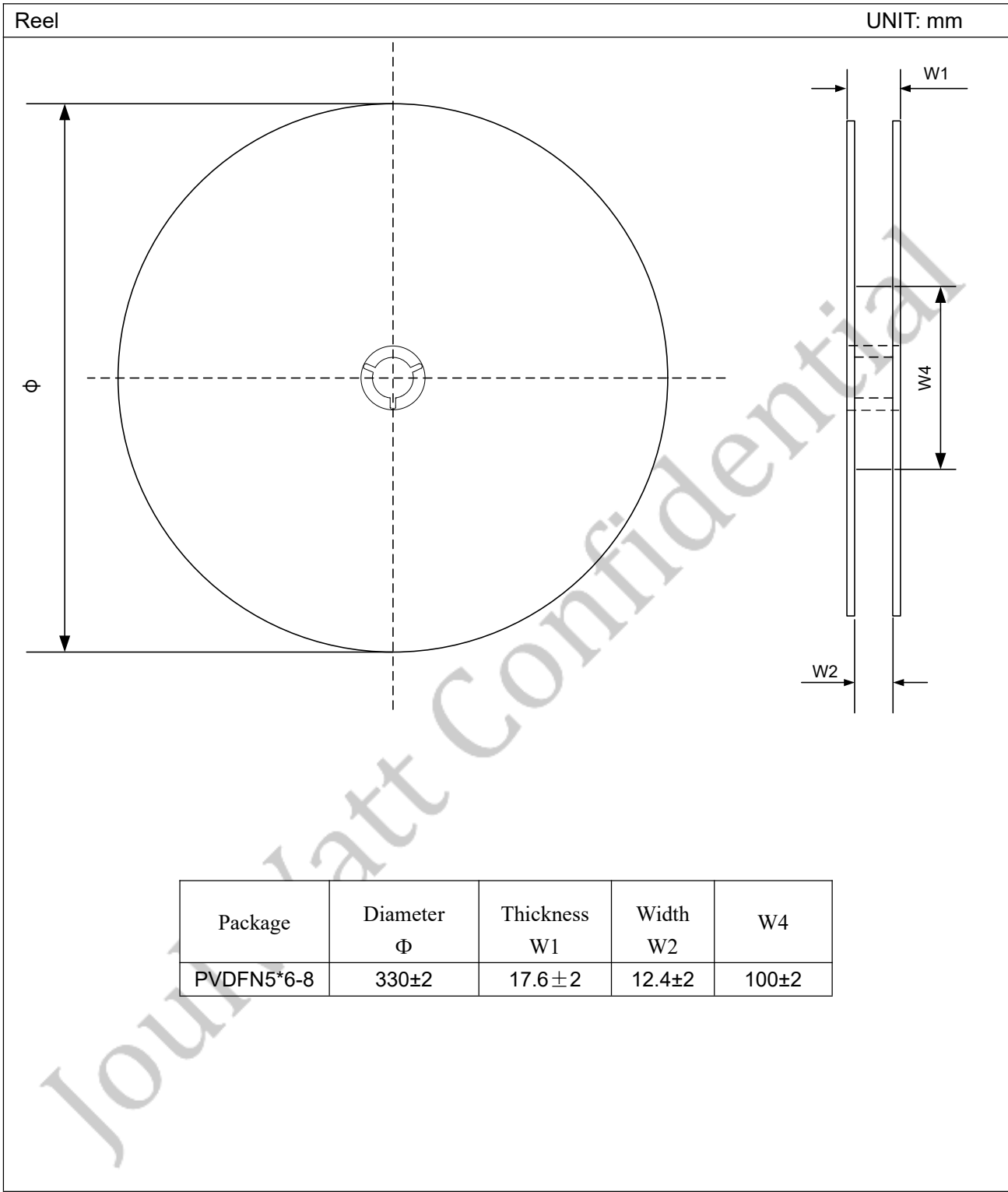
SECTION B-B



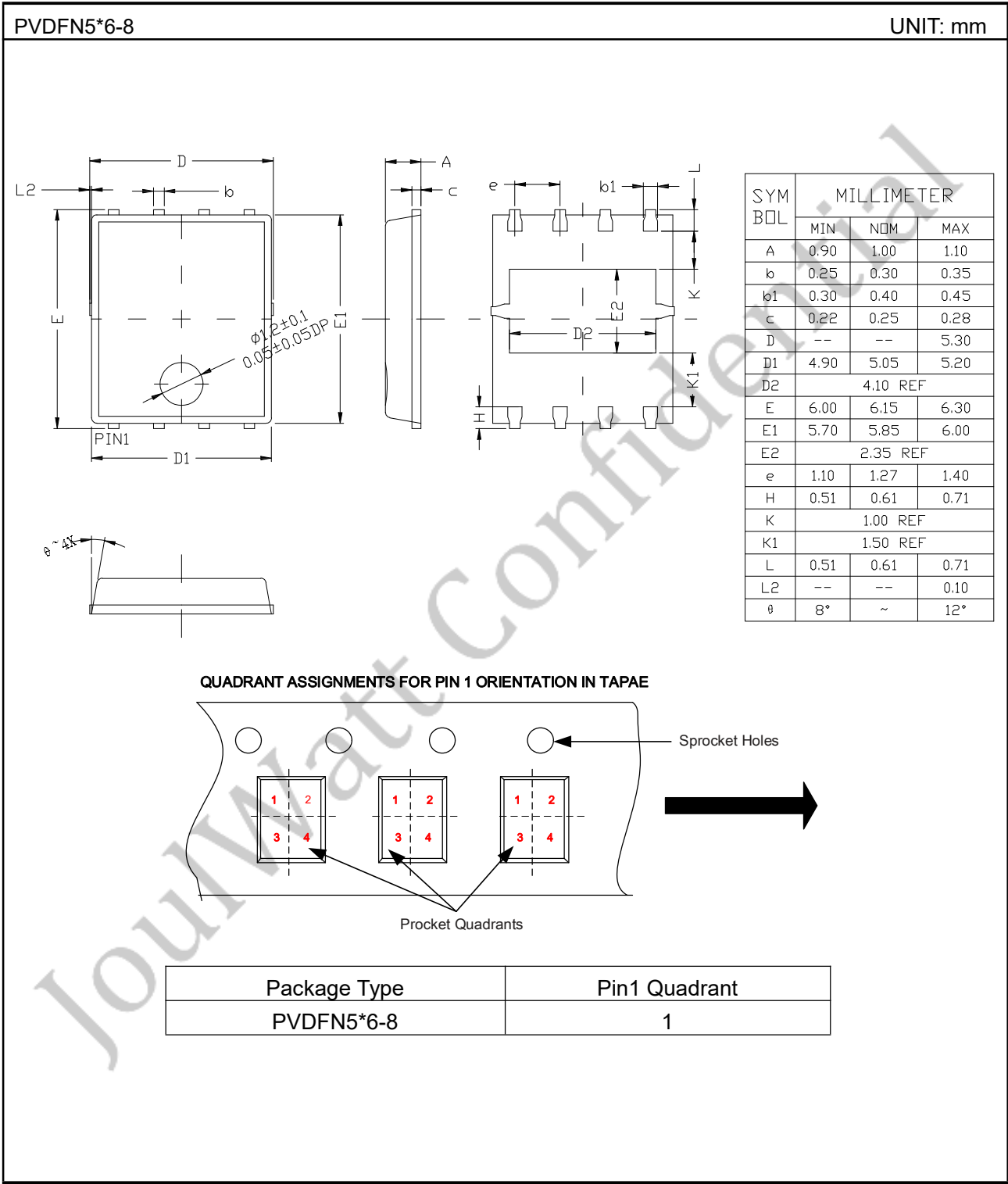
SECTION A-A

- Note :
- 1) The carrier type is black, and colorless transparent.
 - 2) Carrier camber is within 1mm in 100mm.
 - 3) 10 pocket hole pitch cumulative tolerance:±0.20.
 - 4) All dimensions are in mm.

Package	Tape dimensions (mm)											
	P0	P2	P1	A0	B0	W	T	K0	Φ1	Φ2	E	F
PVDFN5*6-8	4.0±0.1	2.0±0.1	8.00±0.10	6.40±0.2	5.42±0.2	12.0±0.3	0.2±0.1	1.25±0.2	1.50min	1.50min	1.75±0.1	5.50±0.10



PACKAGE OUTLINE



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